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NTE198 Silicon NPN Transistor High Voltage Power Transistor

Description:

The NTE198 is a high voltage silicon NPN power transistor in a TO220 type package designed for use as a line operated audio output amplifier, switchmode power supply driver, and other switchmode applications.

Absolute Maximum Ratings:

Collector–Emitter Voltage, V_{CEO}	400V
Collector–Base Voltage, V_{CB}	500V
Emitter–Base Voltage, V_{EB}	5V
Collector Current, I_C	
Continuous	1A
Peak	2A
Base Current, I_B	600mA
Total Power Dissipation ($T_A = +25^\circ\text{C}$), P_D	2W
Derate above $+25^\circ\text{C}$	0.016W/ $^\circ\text{C}$
Total Power Dissipation ($T_C = +25^\circ\text{C}$), P_D	40W
Derate above $+25^\circ\text{C}$	0.32W/ $^\circ\text{C}$
Unclamped Inducting Load Energy, E	20mJ
Operating Junction Temperature Range, T_J	-65° to $+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-65° to $+150^\circ\text{C}$
Thermal Resistance, Junction–to–Case, R_{thJC}	3.125 $^\circ\text{C}/\text{W}$
Thermal Resistance, Junction–to–Ambient, R_{thJA}	62.5 $^\circ\text{C}/\text{W}$

Electrical Characteristics: ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector–Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 30\text{mA}$, $I_B = 0$, Note 1	400	–	–	V
Collector Cutoff Current	I_{CEO}	$V_{CE} = 300\text{V}$, $I_B = 0$	–	–	1	mA
	I_{CES}	$V_{CE} = 500\text{V}$, $V_{BE} = 0$	–	–	1	mA
Emitter Cutoff Current	I_{EBO}	$V_{BE} = 5\text{V}$, $I_C = 0$	–	–	1	mA

Note 1. Pulse test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

Electrical Characteristics (Cont'd): ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
ON Characteristics (Note 1)						
DC Current Gain	h_{FE}	$V_{CE} = 10\text{V}, I_C = 0.3\text{A}$	30	–	150	
		$V_{CE} = 10\text{V}, I_C = 1\text{A}$	10	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1\text{A}, I_B = 0.2\text{A}$	–	–	1.0	V
Base–Emitter ON Voltage	$V_{BE(on)}$	$V_{CE} = 10\text{V}, I_C = 1\text{A}$	–	–	1.5	V
Dynamic Characteristics						
Current Gain–Bandwidth Product	f_T	$V_{CE} = 10\text{V}, I_C = 0.2\text{A}, f = 2\text{MHz}$	10	–	–	MHz
Small–Signal Current Gain	h_{fe}	$V_{CE} = 10\text{V}, I_C = 0.2\text{A}, f = 1\text{kHz}$	25	–	–	

Note 1. Pulse test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

